

Dual N-channel 60 V, 55 mΩ logic level MOSFET

24 February 2015

Product data sheet

1. General description

Dual logic level N-channel MOSFET in an LFPAK56D (Dual Power-SO8) package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- Dual MOSFET
- Q101 Compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True logic level gate with $V_{GS(th)}$ rating of greater than 0.5 V at 175 °C

3. Applications

- 12 V Automotive systems
- Motors, lamps and solenoid control
- Transmission control
- Ultra high performance power switching

4. Quick reference data

Table 1. Quie	ck reference data						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 5 V; T _{mb} = 25 °C; <u>Fig. 2</u>		-	-	16	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	32	W
Static characte	eristics FET1 and FET2						
R _{DSon}	drain-source on-state resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>		-	47.3	55	mΩ
Dynamic characteristics FET1 and FET2							
Q _{GD}	gate-drain charge	$I_D = 5 \text{ A}; V_{DS} = 48 \text{ V}; V_{GS} = 5 \text{ V};$ $T_j = 25 \text{ °C}; \text{ Fig. 14}; \text{ Fig. 15}$		-	2.3	-	nC

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5. Pinning information

Table 2.	Pinning	information		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S1	source1	8 7 6 5	D1 D1 D2 D2
2	G1	gate1		
3	S2	source2	\Box	
4	G2	gate2		
5	D2	drain2		 S1 G1 S2 G2
6	D2	drain2		mbk725
7	D1	drain1	1 2 3 4 LFPAK56D (SOT1205)	
8	D1	drain1		

6. Ordering information

Table 3. Ordering information						
Type number	Package					
	Name	Description	Version			
BUK9K52-60E	LFPAK56D	Plastic single ended surface mounted package (LFPAK56D); 8 leads	SOT1205			

7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK9K52-60E	95260E

8. Limiting values

Table 5.Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{DGR}	drain-gate voltage	R _{GS} = 20 kΩ; T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V _{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-10	10	V
		$T_j \le 175 \ ^{\circ}C; Pulsed$	[1][2]	-15	15	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	32	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	16	А
		T _{mb} = 100 °C; V _{GS} = 5 V; <u>Fig. 2</u>		-	11	А
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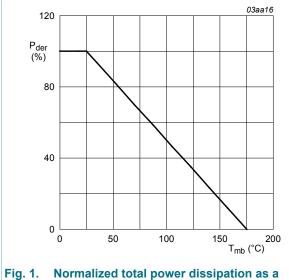
Symbol	Parameter	Conditions		Min	Мах	Unit
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \ \mu$ s; Fig. 3	3	-	64	А
T _{stg}	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
T _{sld(M)}	peak soldering temperature			-	260	°C
Source-drai	in diode FET1 and FET2					
I _S	source current	T _{mb} = 25 °C		-	16	А
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	64	А
Avalanche	ruggedness FET1 and FET2	-				
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$I_D = 16 \text{ A}; V_{sup} \le 60 \text{ V}; V_{GS} = 5 \text{ V};$ $T_{j(init)} = 25 \text{ °C}; Fig. 4$	[3][4]	-	11.9	mJ

Accumulated Pulse duration up to 50 hours delivers zero defect ppm [1]

[2] Significantly longer life times are achieved by lowering T_{i} and or V_{GS}

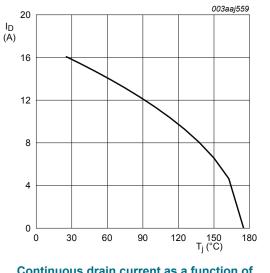
[3] [4] Refer to application note AN10273 for further information

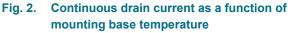
Single-pulse avalanche rating limited by maximum junction temperature of 175 °C



function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

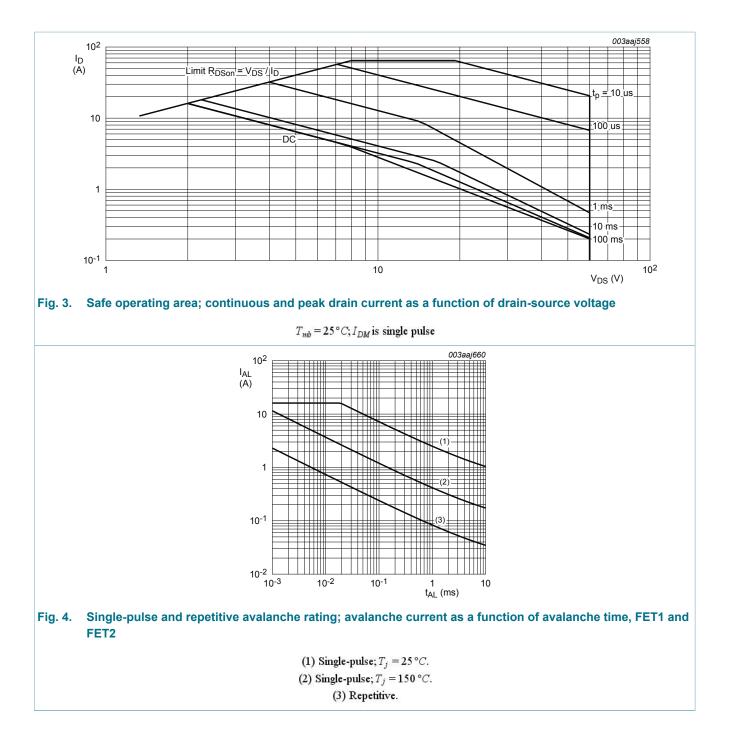




 $V_{GS} \ge 5V$

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9. Thermal characteristics

Table 6. The	Table 6. Thermal characteristics						
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	<u>Fig. 5</u>		-	-	4.68	K/W

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Symbol	Parameter	Conditions	5		Min	Тур	Max	Unit
₹ _{th(j-a)}	thermal resistance from junction to ambient	Minimum for printed circ	ootprint; mounted o cuit board	na	-	95	-	K/W
(K/W)							003aaj557	
10-1	0.1				P	\prod	$\overline{D} = \frac{t_p}{T}$	
10 ⁻²	10 ⁻⁵	10 ⁻⁴	10 ⁻³	10 ⁻²	10 ⁻¹	$t_p \mid T \rightarrow T$ $t_p (s)$		

10. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics FET1 and FET2	· · · · · ·	I.			
V _{(BR)DSS}	drain-source	I_D = 250 µA; V_{GS} = 0 V; T_j = -55 °C	54	-	-	V
	breakdown voltage	I_D = 250 µA; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ Fig. 10; Fig. 11	1.4	1.7	2.1	V
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; Fig. 10; Fig. 11	0.5	-	-	V	
	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; Fig. 10; Fig. 11	-	-	2.45	V	
I _{DSS}	drain leakage current	V_{DS} = 60 V; V_{GS} = 0 V; T_j = 25 °C	-	0.02	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V_{GS} = -10 V; V_{DS} = 0 V; T_j = 25 °C	-	2	100	nA
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state	$V_{GS} = 5 \text{ V}; I_D = 5 \text{ A}; T_j = 25 \text{ °C}; Fig. 12$	-	47.3	55	mΩ
resistance	resistance	V _{GS} = 5 V; I _D = 5 A; T _j = 175 °C; Fig. 12; Fig. 13	-	106.9	124.3	mΩ
		V _{GS} = 10 V; I _D = 5 A; T _j = 25 °C; <u>Fig. 12</u>	-	41.4	49	mΩ

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Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Dynamic cl	haracteristics FET1 and FE	T2				
Q _{G(tot)}	total gate charge	I _D = 5 A; V _{DS} = 48 V; V _{GS} = 5 V;	-	5.6	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C; <u>Fig. 14</u> ; <u>Fig. 15</u>	-	1.1	-	nC
Q _{GD}	gate-drain charge	-	-	2.3	-	nC
C _{iss}	input capacitance	V_{GS} = 0 V; V_{DS} = 25 V; f = 1 MHz;	-	544	725	pF
C _{oss}	output capacitance	T _j = 25 °C; <u>Fig. 16</u>	-	74	89	pF
C _{rss}	reverse transfer capacitance	-	-	40	55	pF
t _{d(on)}	turn-on delay time	V_{DS} = 48 V; R _L = 10 Ω; V _{GS} = 5 V;	-	6.2	-	ns
t _r	rise time	$R_{G(ext)} = 5 \Omega; T_j = 25 °C; I_D = 5 A$	-	10.1	-	ns
t _{d(off)}	turn-off delay time	-	-	10.7	-	ns
t _f	fall time	-	-	9	-	ns
Source-dra	in diode FET1 and FET2		II			
V _{SD}	source-drain voltage	I _S = 5 A; V _{GS} = 0 V; T _j = 25 °C; <u>Fig. 17</u>	-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 5 \text{ A}; \text{ d}I_{S}/\text{d}t = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	17.7	-	ns
Q _r	recovered charge	V _{DS} = 30 V; T _j = 25 °C	-	11.6	-	nC

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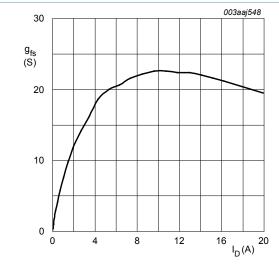


Fig. 6. Forward transconductance as a function of drain current; typical values

 $T_j = 25 \,^{\circ}C; V_{DS} = 15 \,^{\circ}V$

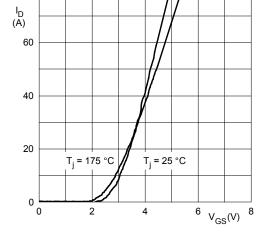
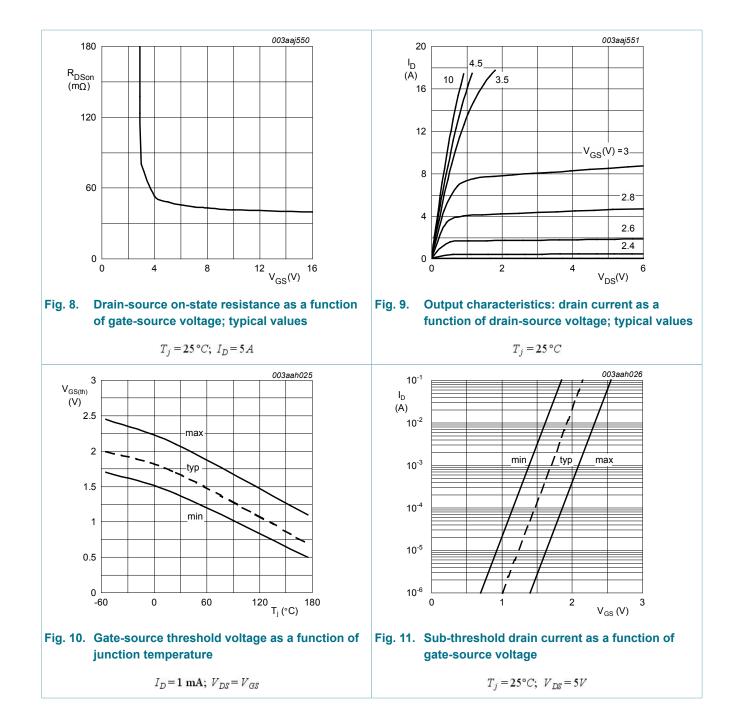


Fig. 7. Transfer characteristics: drain current as a function of gate-source voltage; typical values

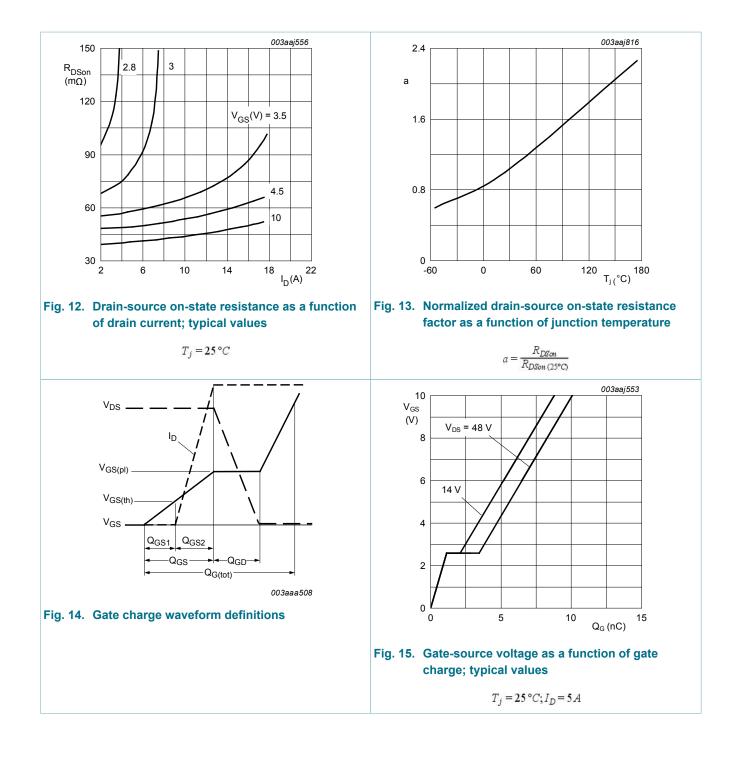
 $V_{DS} = 10V$

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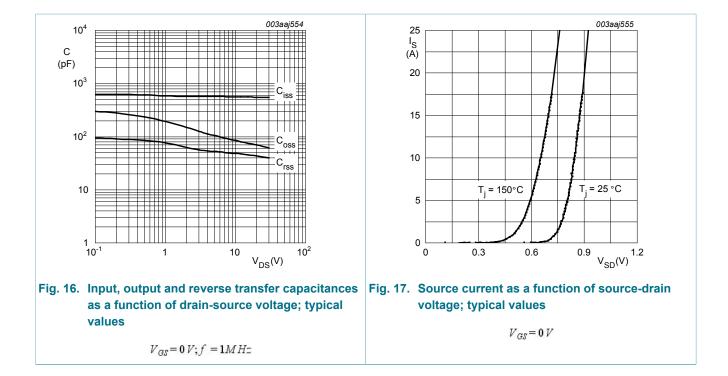
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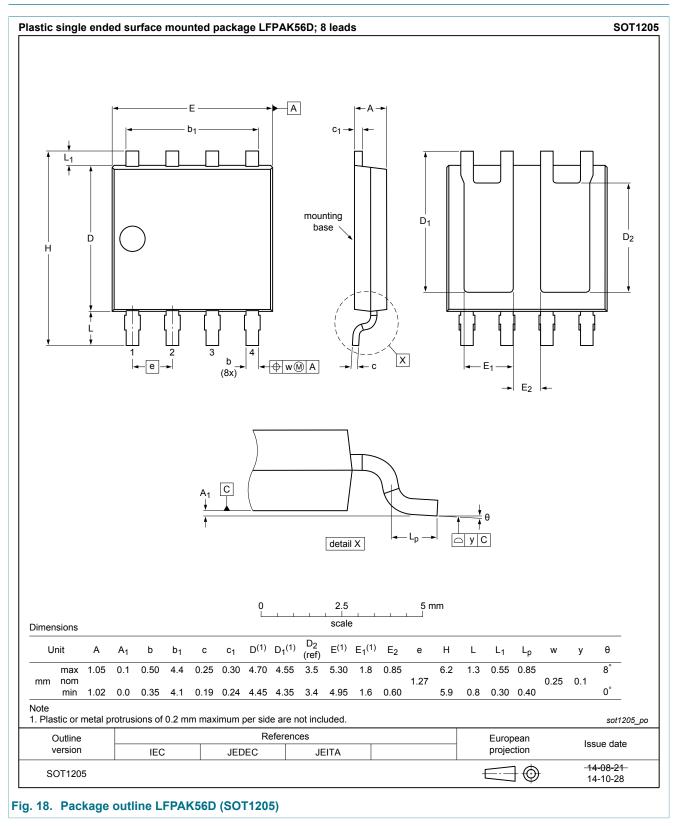
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11. Package outline



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12. Legal information

12.1 Data sheet status

Document status [1][2]	Product status [<u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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